











TS3A5018

SCDS189G - JANUARY 2005 - REVISED MARCH 2015

## TS3A5018 10-Ω Quad SPDT Analog Switch

#### **Features**

- Low ON-State Resistance (10  $\Omega$ )
- Low Charge Injection
- **Excellent ON-State Resistance Matching**
- Low Total Harmonic Distortion (THD)
- 1.8-V to 3.6-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Mode (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)

#### **Applications**

- Sample-and-Hold Circuits
- **Battery-Powered Equipment**
- Audio and Video Signal Routing
- **Communication Circuits**

#### 3 Description

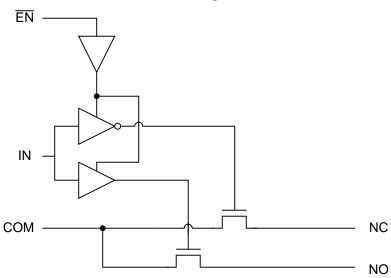
The TS3A5018 device is a quad single-pole doublethrow (SPDT) analog switch that is designed to operate from 1.8 V to 3.6 V. This device can handle digital and analog signals, and signals up to V<sub>+</sub> can be transmitted in either direction.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	SOIC (16)	9.90 mm × 6.00 mm
	SSOP (16)	6.00 mm × 4.90 mm
TS3A5018	TSSOP (16)	5.00 mm × 4.40 mm
133A3016	TVSOP (16)	4.40 mm × 3.60 mm
	UQFN (16)	2.50 mm × 1.80 mm
	VQFN (16)	4.00 mm × 3.50 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Block Diagram**





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#### 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

#### Changes from Revision F (June 2013) to Revision G

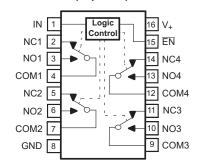
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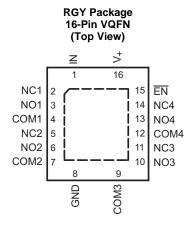
Added Applications, Device Information table, Pin Functions table, ESD Ratings table, Thermal Information table,
Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation
section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and
Mechanical, Packaging, and Orderable Information section.
 Deleted Ordering Information table.

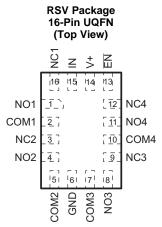


## 5 Pin Configuration and Functions

D, DBQ, DGV and PW Package 16-Pin SOIC, SSOP, TVSOP and TSSOP (Top View)







#### **Pin Functions**

	PIN			
NAME	SOIC, SSOP, TVSOP, VQFN NO.	UQFN NO.	TYPE	DESCRIPTION
COM1	4	2	I/O	Common path for switch
COM2	7	5	I/O	Common path for switch
COM3	9	7	I/O	Common path for switch
COM4	12	10	I/O	Common path for switch
EN	15	13	I	Active-low switch enable input
GND	8	6	_	Ground
IN	1	15	I	Switch path selector input
NC1	2	16	I/O	Normally closed path for switch
NC2	5	3	I/O	Normally closed path for switch
NC3	11	9	I/O	Normally closed path for switch
NC4	14	12	I/O	Normally closed path for switch
NO1	3	1	I/O	Normally open path for switch
NO2	6	4	I/O	Normally open path for switch
NO3	10	8	I/O	Normally open path for switch
NO4	13	11	I/O	Normally open path for switch
V+	16	14	_	Supply voltage



#### 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)(2)

			MIN	MAX	UNIT
V <sub>+</sub>	Supply voltage <sup>(3)</sup>		-0.5	4.6	V
V <sub>NC</sub>					
$V_{NO}$	Analog voltage (3) (4)		-0.5	4.6	V
$V_{\text{COM}}$					
I <sub>K</sub>	Analog port diode current	V <sub>NC</sub> , V <sub>NO</sub> , V <sub>COM</sub> < 0	-50		mA
I <sub>NC</sub>					
$I_{NO}$	ON-state switch current	$V_{NC}$ , $V_{NO}$ , $V_{COM} = 0$ to 7 V	-64	64	mA
$I_{COM}$					
VI	Digital input voltage (3)(4)		-0.5	4.6	V
I <sub>IK</sub>	Digital input clamp current	V <sub>I</sub> < 0	-50		mA
I <sub>+</sub>	Continuous current through V <sub>+</sub>		-100	100	mA
I <sub>GND</sub>	Continuous current through GND		-100	100	mA
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 6.2 ESD Ratings

			VALUE	UNIT
	(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	
V <sub>(ESD)</sub>		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

#### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>I/O</sub>	Switch input and output voltage	0	$V_{+}$	V
V <sub>+</sub>	Supply voltage	1.65	3.6	V
VI	Control input voltage	0	3.6	V
T <sub>A</sub>	Operating temperature	-40	85	°C

#### 6.4 Thermal Information

•								
			TS3A5018					
	THERMAL METRIC (1)	D (SOIC)	DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	RSV (UQFN)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	73	90	120	108	51	184	°C/W

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

<sup>(2)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

<sup>(3)</sup> All voltages are with respect to ground, unless otherwise specified.

<sup>(4)</sup> The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## 6.5 Electrical Characteristics for 3.3-V Supply

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}^{(1)}$ 

	PARAMETER	TEST CON	DITIONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
Analog Switch									
V <sub>COM</sub> , V <sub>NO</sub> , V <sub>NC</sub>	Analog signal range					0		$V_{+}$	V
	ON-state	$0 \le (V_{NC} \text{ or } V_{NO}) \le V_+,$	Switch ON,	25°C	2.1/		7	10	
on	resistance	$I_{COM} = -32 \text{ mA},$	see Figure 17	Full	3 V			12	Ω
	ON-state	$V_{NC}$ or $V_{NO} = 2.1 \text{ V}$ ,	Switch ON,	25°C			0.3	0.8	
∆r <sub>on</sub>	resistance match between channels	$I_{COM} = -32 \text{ mA},$	see Figure 17	Full	3 V			1	Ω
	ON-state	$0 \le (V_{NC} \text{ or } V_{NO}) \le V_+,$	Switch ON,	25°C			5	7	
on(flat)	resistance flatness	$I_{COM} = -32 \text{ mA},$	see Figure 17	Full	3 V			8	Ω
		V <sub>NC</sub> or V <sub>NO</sub> = 1 V,		25°C		-0.1	0.05	0.1	
		$V_{COM} = 3 \text{ V},$ or $V_{NC}$ or $V_{NO} = 3 \text{ V},$	Switch OFF, see Figure 18	Full	3.6 V	-0.2		0.2	
I <sub>NC(OFF)</sub> ,	NC, NO	$V_{COM} = 1 \text{ V},$		2500		2	0.05	2	
I <sub>NO(OFF)</sub>	OFF leakage current	$V_{NC}$ or $V_{NO} = 0$ to 3.6 $V$ ,		25°C		-2	0.05	2	μΑ
		$\begin{array}{c} V_{COM} = 3.6 \text{ V to 0,} \\ \text{or} \\ V_{NC} \text{ or } V_{NO} = 3.6 \text{ V to} \\ 0, \end{array}$	Switch OFF, see Figure 18	Full	0 V	-10		10	
		$V_{COM} = 0 \text{ to } 3.6 \text{ V},$							
		$V_{COM} = 1 \text{ V},$ $V_{NC} \text{ or } V_{NO} = 3 \text{ V},$ or	Switch OFF, see Figure 18	25°C	3.6 V	-0.1	0.05	0.1	
		$V_{COM} = 3 \text{ V},$ $V_{NC} \text{ or } V_{NO} = 3 \text{ V},$	555 T.Iguio 15	Full		-0.2		0.2	
COM(OFF)	COM OFF leakage current	V <sub>COM</sub> = 0 to 3.6 V, V <sub>NC</sub> or V <sub>NO</sub> = 3.6 V to		25°C		-2	0.05	2	μΑ
COMICITY		0, or V <sub>COM</sub> = 3.6 V to 0, V <sub>NC</sub> or V <sub>NO</sub> = 0 to 3.6 V,	Switch OFF, see Figure 18	Full	0 V	-10		10	
		$V_{NC}$ or $V_{NO} = 1 \text{ V}$ ,		25°C		-0.1	0.05	0.1	·
NC(ON), NO(ON)	NC, NO ON leakage current	$V_{COM} = Open,$ or $V_{NC}$ or $V_{NO} = 3 V,$ $V_{COM} = Open,$	Switch ON, see Figure 19	Full	3.6 V	-0.2		0.2	μΑ
		V <sub>COM</sub> = 1 V,		25°C		-0.1	0.05	0.1	
COM(ON)	COM ON leakage current	$V_{NC}$ or $V_{NO}$ = Open, or $V_{COM}$ = 3 V, $V_{NC}$ or $V_{NO}$ = Open,	Switch ON, see Figure 19	Full	3.6 V	-0.2		0.2	μΑ
V <sub>IH</sub>	Input logic high			Full		2		V <sub>+</sub>	V
/ <sub>IL</sub>	Input logic low			Full		0		0.8	V
I <sub>IH</sub> , I <sub>IL</sub>	Input leakage current	$V_1 = V_{\perp}$ or 0		25°C	3.6 V	-1	0.05	1	μA
'IH' 'IL	input leakage current	V  = V <sub>+</sub> 01 0		Full	3.0 V	-1		1	μ/ \
Q <sub>C</sub>	Charge injection	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 0.1 \text{ nF},$ see Figure 26	25°C	3.3 V		2		pC
ONC(OFF),	NC, NO OFF capacitance	$V_{NC}$ or $V_{NO} = V_{+}$ or GND,	Switch OFF, see Figure 20	25°C	3.3 V		4.5		pF
COM(OFF)	COM OFF capacitance	V <sub>COM</sub> = V <sub>+</sub> or GND,	Switch OFF, see Figure 20	25°C	3.3 V		9		pF
C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	NC, NO ON capacitance	$V_{NC}$ or $V_{NO} = V_{+}$ or GND,	Switch ON, see Figure 20	25°C	3.3 V		16		pF
C <sub>COM(ON)</sub>	COM ON capacitance	$V_{COM} = V_{+} \text{ or GND},$	Switch ON, see Figure 20	25°C	3.3 V		16		pF

<sup>(1)</sup> The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.



#### **Electrical Characteristics for 3.3-V Supply (continued)**

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C (unless otherwise noted)}^{(1)}$ 

	PARAMETER	TEST C	ONDITIONS	TA	V <sub>+</sub>	MIN 7	ΥP	MAX	UNIT
Cı	Digital input capacitance	$V_I = V_+ \text{ or GND},$	See Figure 20	25°C	3.3 V		3		pF
BW	Bandwidth	$R_L = 50 \Omega$ ,	Switch ON, see Figure 22	25°C	3.3 V		300		MHz
O <sub>ISO</sub>	OFF isolation	$R_L = 50 \Omega$ , $f = 10 MHz$ ,	Switch OFF, see Figure 23	25°C	3.3 V		-48		dB
X <sub>TALK</sub>	Crosstalk	$R_L = 50 \Omega$ , $f = 10 MHz$ ,	Switch ON, see Figure 24	25°C	3.3 V		-48		dB
X <sub>TALK(ADJ)</sub>	Crosstalk adjacent	$R_L = 50 \Omega$ , $f = 10 MHz$ ,	Switch ON, see Figure 25	25°C	3.3 V		-81		dB
THD	Total harmonic distortion	$R_{L} = 600 \Omega,$ $C_{L} = 50 \text{ pF},$	f = 20 Hz to 20 kHz, see Figure 27	25°C	3.3 V	0.2	1%		
	Danish a summer of	V V OND	Oudtab ON OFF	25°C	0.01/		2.5	7	
1+	Positive supply current	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	Full	3.6 V			10	μA

#### 6.6 Electrical Characteristics for 2.5-V Supply

 $V_{+} = 2.3 \text{ V}$  to 2.7 V,  $T_{A} = -40^{\circ}\text{C}$  to 85°C (unless otherwise noted)<sup>(1)</sup>

	PARAMETER	TEST CO	NDITIONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
$V_{COM}, V_{NC}, V_{NO}$	Analog signal range					0		$V_{+}$	V
	ON-state	$0 \le (V_{NC} \text{ or } V_{NO}) \le V_+,$	Switch ON,	25°C	2.3 V		12	20	Ω
on	resistance	$I_{COM} = -24 \text{ mA},$	see Figure 17	Full	2.3 V			22	12
	ON-state	$V_{NC}$ or $V_{NO} = 1.6 \text{ V}$ ,	Switch ON,	25°C	0.01/		0.3	1	0
∆r <sub>on</sub>	resistance match between channels	$I_{COM} = -24 \text{ mA},$	see Figure 17	Full	2.3 V			2	Ω
	ON-state	$0 \le (V_{NC} \text{ or } V_{NO}) \le V_+,$	Switch ON,	25°C	0.0.1/		14	18	0
on(flat)	resistance flatness	$I_{COM} = -24 \text{ mA},$	see Figure 17	Full	2.3 V			20	Ω
		$V_{NC}$ or $V_{NO} = 0.5 \text{ V}$ ,		25°C		-0.1	0.05	0.1	
I <sub>NC(OFF)</sub> ,	NC, NO	DFF leakage current $V_{NC}$ or $V_{NO} = 0$ to 3.6 V,	Full	2.7 V	-0.2		0.2		
NO(OFF)	OFF leakage current			25°C		-2	0.05	2	μΑ
		$\begin{array}{c} V_{COM} = 3.6 \text{ V to 0,} \\ \text{or} \\ V_{NC} \text{ or } V_{NO} = 3.6 \text{ V to 0,} \\ V_{COM} = 0 \text{ to } 3.6 \text{ V,} \\ \end{array} \\ \begin{array}{c} \text{Switch OFF,} \\ \text{see Figure 18} \\ \end{array}$		Full	0 V	-10		10	
	COM	$V_{COM} = 0.5 \text{ V},$		25°C		-0.1	0.05	0.1	
		$\begin{array}{c} V_{NC} \text{ or } V_{NO} = 2.2 \text{ V}, \\ \text{ or } \\ V_{COM} = 2.2 \text{ V}, \\ \text{ COM} \\ \end{array} \qquad \begin{array}{c} \text{Switch C} \\ \text{ see Figure} \\ \text{ VNC or } V_{NO} = 0.5 \text{ V}, \end{array}$	Switch OFF, see Figure 18	Full	2.7 V	-0.2		0.2	
COM(OFF)	OFF leakage current	$V_{COM} = 0 \text{ to } 3.6 \text{ V},$		25°C		-2	0.05	2	μΑ
		$\begin{split} &V_{NC} \text{ or } V_{NO} = 3.6 \text{ V to 0,} \\ &\text{or} \\ &V_{COM} = 3.6 \text{ V to 0,} \\ &V_{NC} \text{ or } V_{NO} = 0 \text{ to } 3.6 \text{ V,} \end{split}$	Switch OFF, see Figure 18	Full	0 V	-10		10	
		$V_{NC}$ or $V_{NO} = 0.5 \text{ V}$ ,		25°C		-0.1	0.05	0.1	
NC(ON), NO(ON)	NC, NO ON leakage ON ON leakage ON	Switch ON, see Figure 19	Full	2.7 V	-0.2		0.2	μА	
		$V_{COM} = 0.5 \text{ V},$		25°C		-0.1	0.05	0.1	
COM(ON)	COM ON leakage current	$\begin{split} &V_{NC} \text{ or } V_{NO} = \text{Open,} \\ &\text{ or } \\ &V_{COM} = 2.2 \text{ V,} \\ &V_{NC} \text{ or } V_{NO} = \text{Open,} \end{split}$	Switch ON, see Figure 19	Full	2.7 V	-0.2		0.2	μΑ
V <sub>IH</sub>	Input logic high			Full		1.7		V <sub>+</sub>	V
V <sub>IL</sub>	Input logic low			Full		0		0.7	V

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.



#### **Electrical Characteristics for 2.5-V Supply (continued)**

 $V_{+} = 2.3 \text{ V}$  to 2.7 V,  $T_{A} = -40^{\circ}\text{C}$  to 85°C (unless otherwise noted)<sup>(1)</sup>

	PARAMETER	TEST CON	IDITIONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
L. L.	Input leakage current	$V_1 = V_+ \text{ or } 0$		25°C	2.7 V	-0.1	0.05	0.1	μA
I <sub>IH</sub> , I <sub>IL</sub>	input leakage current	V  = V <sub>+</sub> OI O		Full	2.7 V	-1		1	μΑ
$Q_C$	Charge injection	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 0.1 \text{ nF},$ see Figure 26	25°C	2.5 V		1		pC
$\begin{matrix} C_{NC(OFF)}, \\ C_{NO(OFF)} \end{matrix}$	NC, NO OFF capacitance	$V_{NC}$ or $V_{NO} = V_{+}$ or GND,	Switch OFF, see Figure 20	25°C	2.5 V		3		pF
C <sub>COM(OFF)</sub>	COM OFF capacitance	$V_{COM} = V_{+}$ or GND,	Switch OFF, see Figure 20	25°C	2.5 V		9		pF
C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	NC, NO ON capacitance	$V_{NC}$ or $V_{NO} = V_{+}$ or GND,	Switch ON, see Figure 20	25°C	2.5 V		16		pF
C <sub>COM(ON)</sub>	COM ON capacitance	$V_{COM} = V_{+}$ or GND,	Switch ON, see Figure 20	25°C	2.5 V		16		pF
C <sub>I</sub>	Digital input capacitance	$V_I = V_+ \text{ or GND},$	See Figure 20	25°C	2.5 V		3		pF
BW	Bandwidth	$R_L = 50 \Omega$ ,	Switch ON, see Figure 22	25°C	2.5 V		300		MHz
O <sub>ISO</sub>	OFF isolation	$R_L = 50 \Omega$ , f = 10 MHz,	Switch OFF, see Figure 23	25°C	2.5 V		-48		dB
X <sub>TALK</sub>	Crosstalk	$R_L = 50 \Omega$ , f = 10 MHz,	Switch ON, see Figure 24	25°C	2.5 V		-48		dB
X <sub>TALK(ADJ)</sub>	Crosstalk adjacent	$R_L = 50 \Omega$ , f = 10 MHz,	Switch ON, see Figure 25	25°C	3.3 V		-81		dB
THD	Total harmonic distortion	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, see Figure 27	25°C	2.5 V		0.33%		
	Positive supply current	$V_1 = V_+$ or GND,	Switch ON or OFF	25°C	2.7 V		2.5	7	μA
I <sub>+</sub>	i ositive supply culterit	VI - V+ OI GIND,	SWILLII ON OF OFF	Full	Z.1 V		·	10	μA

#### 6.7 Electrical Characteristics for 2.1-V Supply

 $V_{+}$  = 2.00 V to 2.20 V,  $T_{A}$  = -40°C to 85°C (unless otherwise noted)<sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	TA	V <sub>+</sub>	MIN	TYP MAX	UNIT
$V_{IH}$	Input logic high		Full		1.2	4.3	V
$V_{IL}$	Input logic low		Full		0	0.5	V

<sup>(1)</sup> The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

### 6.8 Electrical Characteristics for 1.8-V Supply

 $V_{+} = 1.65 \text{ V}$  to 1.95 V,  $T_{A} = -40 ^{\circ}\text{C}$  to 85  $^{\circ}\text{C}$  (unless otherwise noted) $^{(1)}$ 

PARAMETER		TEST C	ONDITIONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
V <sub>COM</sub> , V <sub>NC</sub> , V <sub>NO</sub>	Analog signal range					0		V <sub>+</sub>	V
_	ON-state	$0 \le (V_{NC} \text{ or } V_{NO}) \le V_+,$	Switch ON,	25°C	1.65 V		5.5	8	Ω
r <sub>on</sub>	resistance	$I_{COM} = -32 \text{ mA},$	see Figure 17	Full	1.00 V			14.55	12
	ON-state			25°C			0.3	1	
$\Delta r_{on}$	resistance match between channels	$V_{NC}$ or $V_{NO} = 1.5 \text{ V}$ , $I_{COM} = -32 \text{ mA}$ ,	Switch ON, see Figure 17	Full	1.65 V			1.2	Ω
	ON-state	$0 \le (V_{NC} \text{ or } V_{NO}) \le V_+,$	Switch ON.	25°C			2.7	5.5	
r <sub>on(flat)</sub>	resistance flatness	$I_{COM} = -32 \text{ mA},$	see Figure 17	Full	1.65 V			7.3	Ω

Product Folder Links: TS3A5018

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.



#### **Electrical Characteristics for 1.8-V Supply (continued)**

 $V_{+}$  = 1.65 V to 1.95 V,  $T_{A}$  = -40°C to 85°C (unless otherwise noted)<sup>(1)</sup>

P/	ARAMETER	TEST COM	NDITIONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
		$V_{NC}$ or $V_{NO} = 0.3 \text{ V}$ , $V_{COM} = 1.65 \text{ V}$ ,		25°C		-0.25	0.03	0.25	
I <sub>NC(OFF)</sub> ,	NC, NO OFF leakage	or V <sub>NC</sub> or V <sub>NO</sub> = 1.65V, V <sub>COM</sub> = 0.3 V,	Switch OFF, see Figure 18	Full	1.95 V	-4.5		4.5	μA
I <sub>NO(OFF)</sub>	current	$V_{NC}$ or $V_{NO} = 1.95 \text{ V to 0 V}$ ,		25°C		-0.4	0.01	0.4	μΑ
		$V_{COM} = 0 \text{ V to } 1.95 \text{ V},$ or $V_{NC}$ or $V_{NO} = 0 \text{ V to } 1.95 \text{ V},$ $V_{COM} = 1.95 \text{ V to } 0 \text{ V},$	Switch OFF, see Figure 18	Full	0 V	-6.5		6.5	
		$V_{COM} = 1.65 \text{ V},$		25°C		-0.4	0.02	0.4	
	COM OFF leakage	$V_{NC}$ or $V_{NO} = 0.3V$ , or $V_{COM} = 0.3 V$ , $V_{NC}$ or $V_{NO} = 1.65V$ ,	Switch OFF, see Figure 18	Full	1.95 V	-0.9		0.9	μA
I <sub>COM(OFF)</sub>	current	$V_{COM} = 0 \text{ V to } 1.95 \text{ V},$		25°C		-0.4	0.02	0.4	μπ
		$V_{NC}$ or $V_{NO} = 1.95$ V to 0 V, or $V_{COM} = 1.95$ V to 0, $V_{NC}$ or $V_{NO} = 0$ to 1.95 V,	Switch OFF, see Figure 18	Full	0 V	-4.5		4.5	
		$V_{NC}$ or $V_{NO} = 0.3 \text{ V}$ ,		25°C		-2.	0.02	2	
I <sub>NC(ON)</sub> , I <sub>NO(ON)</sub>	NC, NO ON leakage current	$V_{COM} = Open,$ or $V_{NC}$ or $V_{NO} = 1.65 V,$ $V_{COM} = Open,$	Switch ON, see Figure 19	Full	1.95 V	-2	0.02	2	μΑ
		$V_{COM} = 0.3 \text{ V},$		25°C		-4.5		4.5	
I <sub>COM(ON)</sub>	COM ON leakage current	$\begin{split} &V_{NC} \text{ or } V_{NO} = \text{Open,} \\ &\text{ or } \\ &V_{COM} = 1.65 \text{ V,} \\ &V_{NC} \text{ or } V_{NO} = \text{Open,} \end{split}$	Switch ON, see Figure 19	Full	1.95 V				μΑ
V <sub>IH</sub>	Input logic high	V <sub>I</sub> = V <sub>+</sub> or GND		Full	1.95 V	1		3.6	V
V <sub>IL</sub>	Input logic low			Full	1.95 V	0		0.4	V
	Input leakage	$V_1 = V_+ \text{ or } 0$		25°C	4.05.V	-0.1	0.01	0.1	
I <sub>IH</sub> , I <sub>IL</sub>	current	v <sub>1</sub> = v <sub>+</sub> 01 0		Full	1.95 V	-2.1		2.1	μA

#### 6.9 Switching Characteristics for 3.3-V Supply

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS			V <sub>+</sub>	MIN	TYP	MAX	UNIT
		V - 2 V	C - 25 pE	25°C	3.3 V	2.5	3.5	8	
t <sub>ON</sub> Turno	Turnon time	$V_{COM} = 2 V,$ $R_L = 300 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 21	Full	3 V to 3.6 V	2.5		9	ns
		V 2V	C 25 pC	25°C	3.3 V	0.5	2	6.5	
t <sub>OFF</sub> Tui	Turnoff time	$V_{COM} = 2 \text{ V},$ $R_L = 300 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 21	Full	3 V to 3.6 V	0.5		7	ns

#### 6.10 Switching Characteristics for 2.5-V Supply

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TES	T CONDITIONS	TA	V <sub>+</sub>	MIN	TYP	MAX	UNIT
	Vac 1 5		5.7		2.5 V	2.5	5	9.5	
t <sub>ON</sub> Turnon time	$V_{COM} = 1.5 \text{ V},$ $R_L = 300 \Omega,$	C <sub>L</sub> = 35 pF, see Figure 21	Full	2.3 V to 2.7 V	2.5		10.5	ns	
		\/ _1 <b>E</b> \/	C - 25 nE	25°C	2.5 V	0.5	3	7.5	
t <sub>OFF</sub> Tu	Turnoff time	$V_{COM} = 1.5 \text{ V},$ $R_L = 300 \Omega,$	C <sub>L</sub> = 35 pF, see Figure 21		2.3 V to 2.7 V	0.5		9	ns



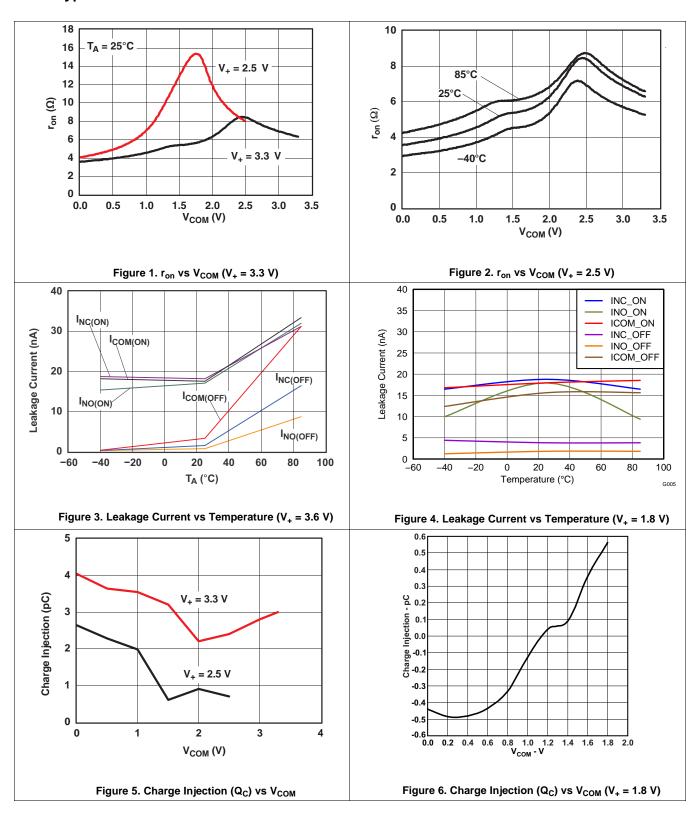
## 6.11 Switching Characteristics for 1.8-V Supply

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST	CONDITIONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
				25°C	1.8 V		14.1	49.3	
t <sub>ON</sub>	Turnon time	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 21	Full	1.65 V to 1.95 V		49.3	56.7	ns
				25°C	1.8 V		16.1	26.5	
t <sub>OFF</sub>	Turnoff time	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 21	Full	1.65 V to 1.95 V			31.2	ns
				25°C	1.8 V	5.3	18.4	58	
t <sub>BBM</sub>	Break-before- make time	$V_{NC} = V_{NO} = V_{+}/2,$ $R_{L} = 50 \Omega,$	$C_L = 35 \text{ pF},$ see Figure 21	Full	1.65 V to 1.95 V			58	ns

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#### 6.12 Typical Characteristics

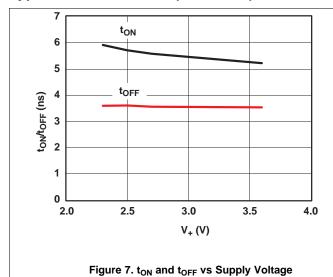


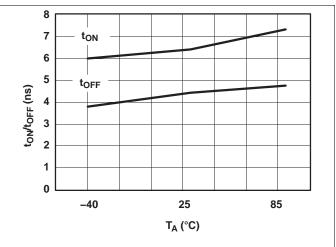
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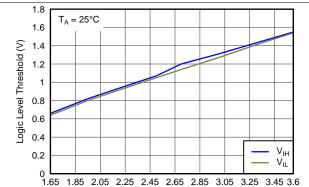
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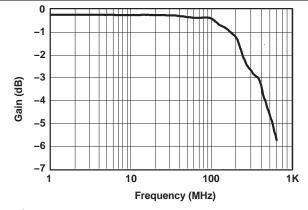
#### **Typical Characteristics (continued)**

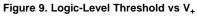












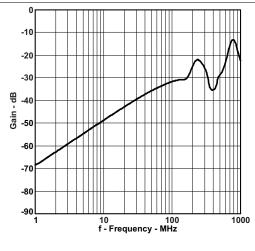


Figure 11. OFF Isolation vs Frequency  $(V_{+} = 1.8 \text{ V})$ 

Figure 10. Gain vs Frequency Bandwidth (V<sub>+</sub> = 3.3 V)

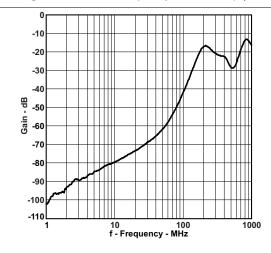


Figure 12. Crosstalk Adjacent vs Frequency (V<sub>+</sub> = 1.8 V)

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#### **Typical Characteristics (continued)**

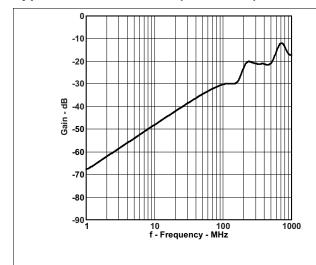


Figure 13. Crosstalk vs Frequency (V<sub>+</sub> = 1.8 V)

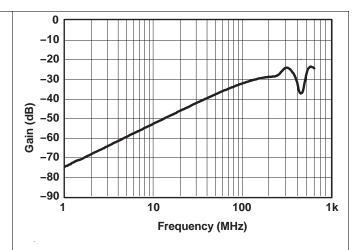


Figure 14. OFF Isolation vs Frequency  $(V_+ = 3.3 \text{ V})$ 

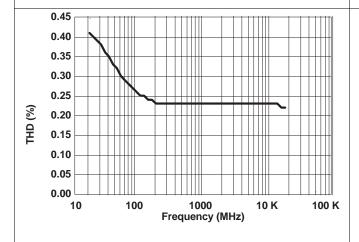


Figure 15. Total Harmonic Distortion vs Frequency

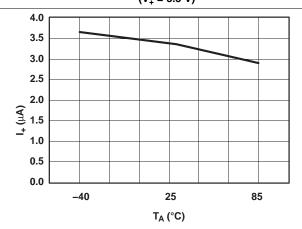


Figure 16. Power-Supply Current vs Temperature  $(V_+ = 3.3 \text{ V})$ 

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#### 7 Parameter Measurement Information

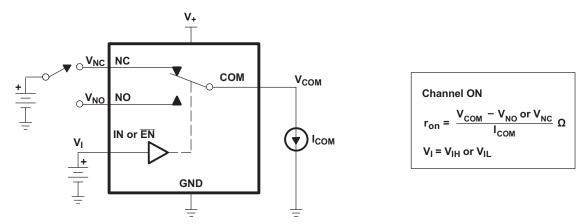


Figure 17. ON-State Resistance (ron)

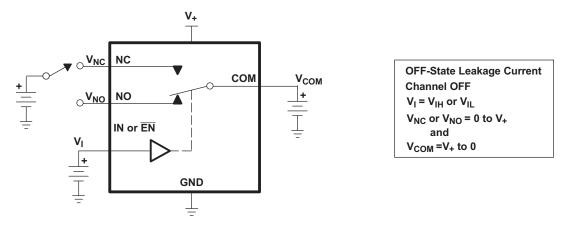


Figure 18. OFF-State Leakage Current ( $I_{COM(OFF)}$ ,  $I_{NC(OFF)}$ ,  $I_{NO(OFF)}$ )

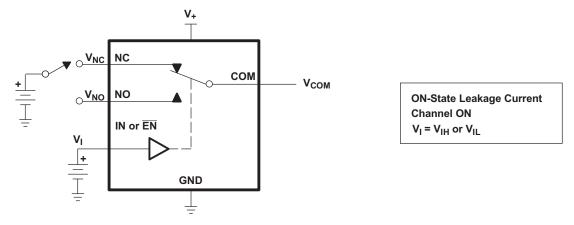


Figure 19. ON-State Leakage Current ( $I_{COM(ON)}$ ,  $I_{NC(ON)}$ )



#### **Parameter Measurement Information (continued)**

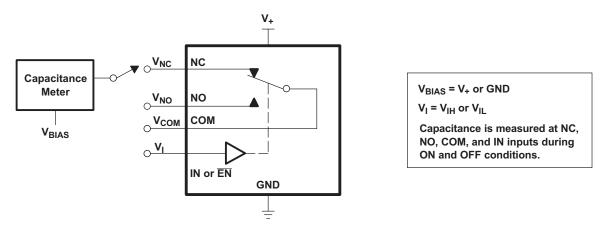
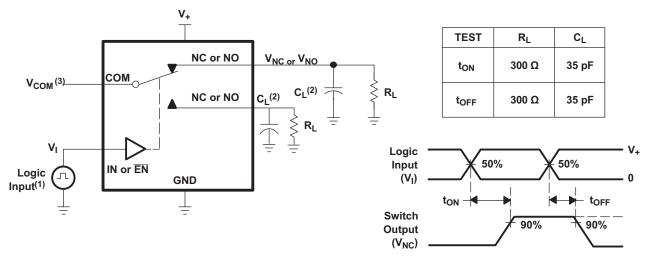


Figure 20. Capacitance (C<sub>I</sub>,  $C_{COM(OFF)}$ ,  $C_{COM(ON)}$ ,  $C_{NC(OFF)}$ ,  $C_{NC(ON)}$ )



- (1) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f < 5 \text{ ns}$ ,  $t_f < 5 \text{ ns}$ .
- (2)  $C_L$  includes probe and jig capacitance.
- (3) See Electrical Characteristics for V<sub>COM</sub>.

Figure 21. Turnon (t<sub>ON</sub>) and Turnoff Time (t<sub>OFF</sub>)

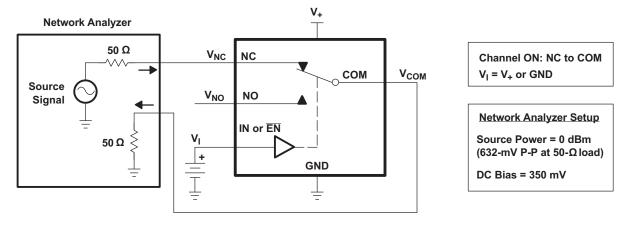
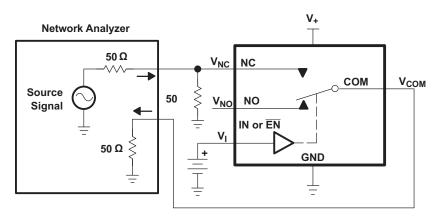


Figure 22. Bandwidth (BW)

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#### **Parameter Measurement Information (continued)**



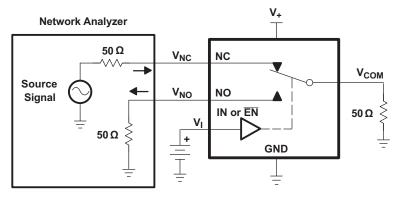
Channel OFF: NC to COM

V<sub>I</sub> = V<sub>+</sub> or GND

**Network Analyzer Setup** 

Source Power = 0 dBm (632-mV P-P at 50-Ωload) DC Bias = 350 mV

Figure 23. OFF Isolation (O<sub>ISO</sub>)

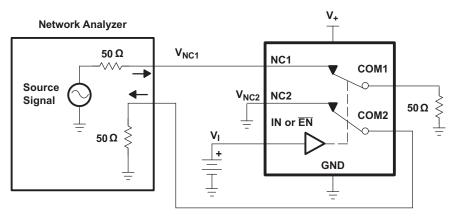


Channel ON: NC to COM
Channel OFF: NO to COM
V<sub>I</sub> = V<sub>+</sub> or GND

#### **Network Analyzer Setup**

Source Power = 0 dBm (632-mV P-P at  $50-\Omega \log d$ ) DC Bias = 350 mV

Figure 24. Crosstalk (X<sub>TALK</sub>)



Channel ON: NC to COM

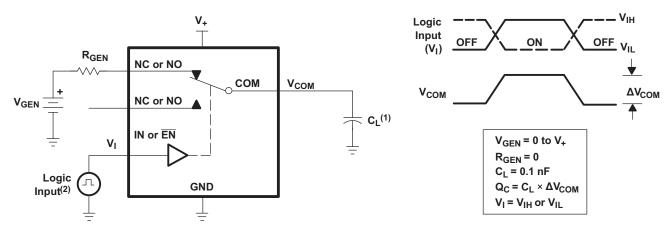
#### Network Analyzer Setup

Source Power = 0 dBm (632 mV P-P at  $50 \Omega$  load) DC Bias = 350 mV

Figure 25. Crosstalk Adjacent

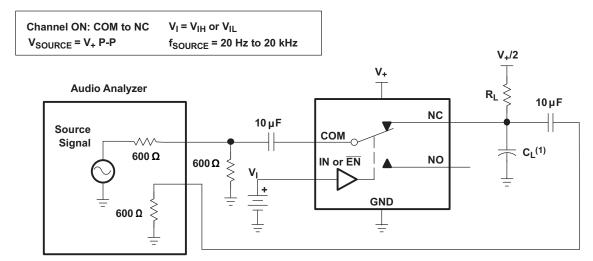


#### **Parameter Measurement Information (continued)**



- (1) C<sub>L</sub> includes probe and jig capacitance.
- (2) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_r < 5 \text{ ns}$ ,  $t_f < 5 \text{ ns}$ .

Figure 26. Charge Injection (Q<sub>C</sub>)



(1) C<sub>L</sub> includes probe and jig capacitance.

Figure 27. Total Harmonic Distortion (THD)

Product Folder Links: TS3A5018

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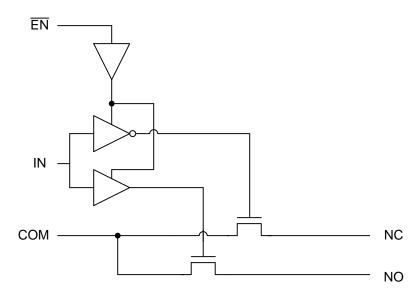
### 8 Detailed Description

#### 8.1 Overview

The TS3A5018 is a quad single-pole-double-throw (SPDT) solid-state analog switch. The TS3A5018, like all analog switches, is bidirectional. When powered on, each COM pin is connected to its respective NC pin. For this device, NC stands for *normally closed* and NO stands for *normally open*. The switch is enabled when EN is low. If IN is also low, COM is connected to NC. If IN is high, COM is connected to NO.

The TS3A5018 is a break-before-make switch. This means that during switching, a connection is broken before a new connection is established. The NC and NO pins are never connected to each other.

#### 8.2 Functional Block Diagram (Each Switch)



#### 8.3 Feature Description

The low ON-state resistance, ON-state resistance matching, and charge injection in the TS3A5018 make this switch an excellent choice for analog signals that require minimal distortion. In addition, the low THD allows audio signals to be preserved more clearly as they pass through the device.

The 1.8-V to 3.6-V operation allows compatibility with more logic levels, and the bidirectional I/Os can pass analog signals from 0 V to  $V_{+}$  with low distortion.

#### 8.4 Device Functional Modes

**Table 1. Function Table** 

EN	IN	NO TO COM, COM TO NO	NC TO COM, COM TO NC
L	L	OFF	ON
L	Н	ON	OFF
Н	Х	OFF	OFF



#### 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The TS3A5018 can be used in a variety of customer systems. The TS3A5018 can be used anywhere multiple analog or digital signals must be selected to pass across a single line.

#### 9.2 Typical Application

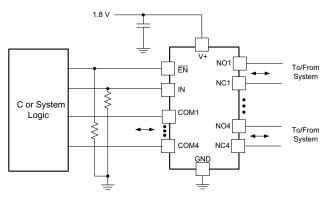


Figure 28. System Schematic for TS3A5018

#### 9.2.1 Design Requirements

In this particular application,  $V_+$  was 1.8 V, although  $V_+$  is allowed to be any voltage specified in *Recommended Operating Conditions*. A decoupling capacitor is recommended on the V+ pin. See *Power Supply Recommendations* for more details.

#### 9.2.2 Detailed Design Procedure

In this application,  $\overline{\text{EN}}$  and IN are, by default, pulled low to GND. Choose these resistor sizes based on the current driving strength of the GPIO, the desired power consumption, and the switching frequency (if applicable). If the GPIO is open-drain, use pullup resistors instead.

#### 9.2.3 Application Curve

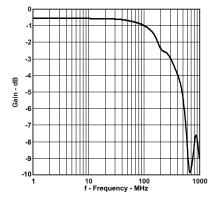


Figure 29. Gain vs Frequency Bandwidth ( $V_{\perp} = 1.8 \text{ V}$ )



#### 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions.

Each V<sub>CC</sub> terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF bypass capacitor is recommended. If there are multiple pins labeled V<sub>CC</sub>, then a 0.01-μF or 0.022- $\mu$ F capacitor is recommended for each  $V_{CC}$  because the VCC pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example V<sub>CC</sub> and V<sub>DD</sub>, a 0.1-µF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

#### Layout 11

#### 11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self-inductance of the trace — resulting in the reflection. It is a given that not all PCB traces can be straight, and so they will have to turn corners. Below figure shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

Unused switch I/Os, such as NO, NC, and COM, can be left floating or tied to GND. However, the IN and EN pins must be driven high or low. Due to partial transistor turnon when control inputs are at threshold levels, floating control inputs can cause increased I<sub>CC</sub> or unknown switch selection states.

#### 11.2 Layout Example

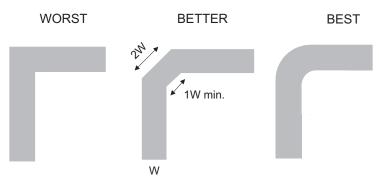


Figure 30. Trace Example



## 12 Device and Documentation Support

## 12.1 Device Support

#### 12.1.1 Device Nomenclature

**Table 2. Parameter Description** 

ViH   Minimum input voltage for logic high for the control input (IN, EN)	SYMBOL	DESCRIPTION
V <sub>NO</sub> Voltage at NO fon Resistance between COM and NC or NO ports when the channel is ON Difference of r <sub>ros</sub> between channels in a specific device r <sub>on(flig)</sub> Difference between the maximum and minimum value of r <sub>on</sub> in a channel over the specified range of conditions l <sub>NC(OFF)</sub> Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open Leakage current measured at the COM port, with the corresponding channel (NO to COM) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the ON state and the output (NC or NO) open  V <sub>H</sub> Maximum input voltage for logic logic high for the control input (IN, EN)  V <sub>1</sub> Leakage current measured at the control input (IN, EN)  Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.  Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or	V <sub>COM</sub>	Voltage at COM
ron Argn Difference of r <sub>m</sub> between COM and NC or NO ports when the channel is ON Difference of r <sub>m</sub> between channels in a specific device ronglaugh Difference between the maximum and minimum value of r <sub>on</sub> in a channel over the specified range of conditions l <sub>NC(OFF)</sub> Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state Leakage current measured at the control input (IN, EN)  V <sub>II</sub> Maximum input voltage for logic low for the control input (IN, EN)  V <sub>II</sub> V <sub>II</sub> Leakage current measured at the control input (IN, EN)  Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning OFF.  Charge injection, O <sub>C</sub> = C <sub>L</sub> × ΔV <sub>COM</sub> , C <sub>L</sub> is the load capacitance and ΔV <sub>COM</sub> is the change in analog output voltage.  Charge injection is a measurement of unwanted signal coupling from the control (IN) in the analog (NC or NO) output. This is measured in the NC port when the correspondin	V <sub>NC</sub>	Voltage at NC
Difference of r <sub>on</sub> between channels in a specific device	V <sub>NO</sub>	Voltage at NO
Incicipation of the service of the maximum and minimum value of ron in a channel over the specified range of conditions Incicops	r <sub>on</sub>	Resistance between COM and NC or NO ports when the channel is ON
INCIGOFF    Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state	$\Delta r_{on}$	Difference of r <sub>on</sub> between channels in a specific device
Inci(ON)   Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open	r <sub>on(flat)</sub>	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
No(COM)   (COM) open     I <sub>NO(COFF)</sub>   Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state     I <sub>NO(CN)</sub>   Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open     I <sub>COM(OFF)</sub>   Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state     I <sub>COM(ON)</sub>   Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state     I <sub>COM(ON)</sub>   Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state     I <sub>COM(ON)</sub>   Maximum input voltage for logic high for the control input (IN, EN)     V <sub>IL</sub>   Maximum input voltage for logic low for the control input (IN, EN)     I <sub>IH</sub> , I <sub>IL</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IH</sub> , I <sub>IL</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Voltage at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     I <sub>IV</sub>   Leakage current measured at the control input (IN, EN)     Capacitance at the NC port when the corresponding channel (NC to COM) is OFF	I <sub>NC(OFF)</sub>	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state
I <sub>NO(ON)</sub>   Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open	I <sub>NC(ON)</sub>	
ICOM(OFF)   Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state	I <sub>NO(OFF)</sub>	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state
IcoM(ON)   Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the ON state and the output (NC or NO) open	I <sub>NO(ON)</sub>	
ViH   Minimum input voltage for logic high for the control input (IN, EN)	I <sub>COM(OFF)</sub>	Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state
V <sub>IL</sub> Maximum input voltage for logic low for the control input (IN, EN)  V <sub>I</sub> Voltage at the control input (IN, EN)  I <sub>IH</sub> , I <sub>IL</sub> Leakage current measured at the control input (IN, EN)  toN  Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.  Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.  Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q <sub>C</sub> = C <sub>L</sub> × ΔV <sub>COM</sub> , C <sub>L</sub> is the load capacitance and ΔV <sub>COM</sub> is the change in analog output voltage.  C <sub>NCIOFF</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is OFF  C <sub>NCION</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is ON  Capacitance at the NC port when the corresponding channel (NO to COM) is ON  C <sub>COMIOFF</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is ON  C <sub>COMIOFF</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COMION</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>COMION</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>COMION</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>COMION</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  Capacitance at the COM port when the corresponding channel (NC to COM) is ON  Capacitance at the COM port when the corresponding channel (COM to NC) is ON  Capacitance of control input (IN, EN)  OFF isolation of the switch is a measureme	I <sub>COM(ON)</sub>	Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the ON state and the output (NC or NO) open
V <sub>I</sub> Voltage at the control input (IN, EN)           I <sub>IH</sub> , I <sub>IL</sub> Leakage current measured at the control input (IN, EN)           toN         Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.           toFF         Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.           Qc         Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Qc = CL × ΔV <sub>COM</sub> , CL is the load capacitance and ΔV <sub>COM</sub> is the change in analog output voltage.           C <sub>NC(OFF)</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is OFF           C <sub>NC(ON)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is ON           C <sub>COM(OFF)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is OFF           C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (NO to COM) is ON           C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF           C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (NO to COM) is ON	$V_{IH}$	Minimum input voltage for logic high for the control input (IN, EN)
I <sub>IH</sub> , I <sub>IL</sub> Leakage current measured at the control input (IN, EN)  ton ton ton time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.  toff Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning OFF.  Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q <sub>C</sub> = C <sub>L</sub> × ΔV <sub>COM</sub> , C <sub>L</sub> is the load capacitance and ΔV <sub>COM</sub> is the change in analog output vlottage.  C <sub>NC(OFF)</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is OFF  C <sub>NC(ON)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  C <sub>NO(ON)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>1</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>1</sub> Corporation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC1). Adjacer  crosstalk is a measurement of unw	V <sub>IL</sub>	Maximum input voltage for logic low for the control input (IN, EN)
Turnon time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.  Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.  Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q <sub>C</sub> = C <sub>L</sub> × ΔV <sub>COM</sub> , C <sub>L</sub> is the load capacitance and ΔV <sub>COM</sub> is the change in analog output voltage.  CNC(OFF)  Capacitance at the NC port when the corresponding channel (NC to COM) is OFF  CNC(ON)  Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  CNO(ON)  Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  CCOM(OFF)  Capacitance at the COM port when the corresponding channel (NO to COM) is OFF  CCOM(ON)  Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  Capacitance at the COM port when the corresponding channel (COM to NC) is ON  Capacitance at the COM port when the corresponding channel (COM to NC) is ON  Capacitance at the COM port when the corresponding channel (COM to NC) is ON  Capacitance at the COM port when the corresponding channel (COM to NC) is ON  Coperity of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NC2). This measured in a specific frequency and in dB.  Than Bandwidth of the switch. This is the frequency in which the gain of an ON channel is ¬3 dB below the DC gain.  Total harmonic d	$V_{I}$	Voltage at the control input (IN, $\overline{\text{EN}}$ )
tope the delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.  Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.  Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q <sub>C</sub> = C <sub>L</sub> × ΔV <sub>COM</sub> , C <sub>L</sub> is the load capacitance and ΔV <sub>COM</sub> is the change in analog output voltage.  C <sub>NC(OFF)</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is OFF  C <sub>NC(ON)</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is ON  C <sub>NO(OFF)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  C <sub>COM(OFF)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is ON  C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>1</sub> Capacitance of control input (IN, EN)  OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measure of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NC2). This measured in a specific frequency and in dB.  BM Bandwidth of the switch. This is the frequency in which the gain of an ON channel is ~3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of ro	$I_{\rm IH},~I_{\rm IL}$	Leakage current measured at the control input (IN, EN)
delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.  Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q <sub>C</sub> = C <sub>L</sub> × ΔV <sub>COM</sub> , C <sub>L</sub> is the load capacitance and ΔV <sub>COM</sub> is the change in analog output voltage.  CNC(OFF) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF  CNC(ON) Capacitance at the NC port when the corresponding channel (NC to COM) is OFF  CNO(ON) Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  CNO(ON) Capacitance at the NC port when the corresponding channel (NO to COM) is ON  CCOM(OFF) Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  CCOM(ON) Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C1 Capacitance of control input (IN, EN)  OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	t <sub>ON</sub>	
$\begin{array}{c} Q_C \\ \text{Output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, Q_C = C_L \times \Delta V_{COM}, C_L is the load capacitance and \Delta V_{COM} is the change in analog output voltage. \\ \hline C_{NC(OFF)} \\ \hline C_{NC(ON)} \\ \hline Capacitance at the NC port when the corresponding channel (NC to COM) is ON \\ \hline C_{NO(OFF)} \\ \hline C_{NO(ON)} \\ \hline Capacitance at the NC port when the corresponding channel (NO to COM) is ON \\ \hline C_{COM(OFF)} \\ \hline C_{COM(OFF)} \\ \hline Capacitance at the NC port when the corresponding channel (NO to COM) is ON \\ \hline C_{COM(OFF)} \\ \hline C_{COM(ON)} \\ \hline Capacitance at the COM port when the corresponding channel (COM to NC) is OFF \\ \hline C_{COM(ON)} \\ \hline C_1 \\ \hline C_1 \\ \hline C_1 \\ \hline C_2 \\ \hline C_2 \\ \hline C_1 \\ \hline C_2 \\ \hline C_2 \\ \hline C_3 \\ \hline C_3 \\ \hline C_4 \\ \hline C_1 \\ \hline C_2 \\ \hline C_3 \\ \hline C_4 \\ \hline C_4 \\ \hline C_5 \\ \hline C_6 \\ \hline C_7 \\ \hline C_8 \\ \hline C_8 \\ \hline C_8 \\ \hline C_9 \\ \hline$	t <sub>OFF</sub>	Turnoff time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.
C <sub>NC(ON)</sub> Capacitance at the NC port when the corresponding channel (NC to COM) is ON C <sub>NO(OFF)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is OFF C <sub>NO(ON)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is ON C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON C <sub>I</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON C <sub>I</sub> Capacitance of control input (IN, EN) O <sub>ISO</sub> OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	$Q_{\mathbb{C}}$	output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input.
C <sub>NO(OFF)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is OFF  C <sub>NO(ON)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is ON  C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF  C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>I</sub> Capacitance of control input (IN, EN)  O <sub>ISO</sub> OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C <sub>NC(OFF)</sub>	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
C <sub>NO(ON)</sub> Capacitance at the NC port when the corresponding channel (NO to COM) is ON C <sub>COM(OFF)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is OFF C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON C <sub>I</sub> Capacitance of control input (IN, EN) O <sub>ISO</sub> OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2) .This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C <sub>NC(ON)</sub>	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
CCOM(OFF)       Capacitance at the COM port when the corresponding channel (COM to NC) is OFF         CCOM(ON)       Capacitance at the COM port when the corresponding channel (COM to NC) is ON         C1       Capacitance of control input (IN, EN)         OISO       OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.         XTALK       Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.         BW       Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.         THD       Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C <sub>NO(OFF)</sub>	Capacitance at the NC port when the corresponding channel (NO to COM) is OFF
C <sub>COM(ON)</sub> Capacitance at the COM port when the corresponding channel (COM to NC) is ON  C <sub>I</sub> Capacitance of control input (IN, EN)  O <sub>ISO</sub> OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C <sub>NO(ON)</sub>	Capacitance at the NC port when the corresponding channel (NO to COM) is ON
Capacitance of control input (IN, EN)  Olso OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	C <sub>COM(OFF)</sub>	Capacitance at the COM port when the corresponding channel (COM to NC) is OFF
OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NC) is ON
frequency, with the corresponding channel (NC to COM) in the OFF state.  Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacer crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	Cı	Capacitance of control input (IN, EN)
x <sub>TALK</sub> crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2) .This measured in a specific frequency and in dB.  BW Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.  Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	O <sub>ISO</sub>	
Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	X <sub>TALK</sub>	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacent crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2) .This is measured in a specific frequency and in dB.
THD mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.	BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
I <sub>+</sub> Static power-supply current with the control (IN) pin at V <sub>+</sub> or GND	THD	mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental
	l <sub>+</sub>	Static power-supply current with the control (IN) pin at V <sub>+</sub> or GND



#### 12.2 Documentation Support

#### 12.2.1 Related Documentation

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

#### 12.3 Trademarks

All trademarks are the property of their respective owners.

#### 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

#### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





10-Jun-2014

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
TS3A5018D	ACTIVE	SOIC	Drawing	16	40	(2) Green (RoHS & no Sb/Br)	(6) CU NIPDAU	(3) Level-1-260C-UNLIM	-40 to 85	(4/5) TS3A5018	Samples
TS3A5018DBQR	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YA018	Samples
TS3A5018DBQRE4	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YA018	Samples
TS3A5018DBQRG4	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YA018	Samples
TS3A5018DE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3A5018	Samples
TS3A5018DGVR	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	YA018	Samples
TS3A5018DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3A5018	Samples
TS3A5018DRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3A5018	Samples
TS3A5018PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	YA018	Samples
TS3A5018PWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	YA018	Samples
TS3A5018PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	YA018	Samples
TS3A5018PWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	YA018	Samples
TS3A5018RGYR	ACTIVE	VQFN	RGY	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YA018	Samples
TS3A5018RGYRG4	ACTIVE	VQFN	RGY	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	YA018	Samples
TS3A5018RSVR	ACTIVE	UQFN	RSV	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	ZUN	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.



#### PACKAGE OPTION ADDENDUM

10-Jun-2014

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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## **PACKAGE MATERIALS INFORMATION**

www.ti.com 18-Oct-2016

#### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

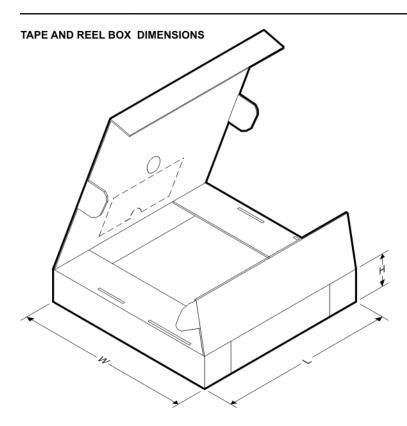
#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3A5018DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
TS3A5018DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
TS3A5018DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TS3A5018PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TS3A5018RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
TS3A5018RSVR	UQFN	RSV	16	3000	180.0	12.4	2.1	2.9	0.75	4.0	12.0	Q1
TS3A5018RSVR	UQFN	RSV	16	3000	177.8	12.4	2.0	2.8	0.7	4.0	12.0	Q1
TS3A5018RSVR	UQFN	RSV	16	3000	180.0	13.2	2.1	2.9	0.75	4.0	12.0	Q1

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\*All dimensions are nominal

					1		
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3A5018DBQR	SSOP	DBQ	16	2500	340.5	338.1	20.6
TS3A5018DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
TS3A5018DR	SOIC	D	16	2500	333.2	345.9	28.6
TS3A5018PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
TS3A5018RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0
TS3A5018RSVR	UQFN	RSV	16	3000	203.0	203.0	35.0
TS3A5018RSVR	UQFN	RSV	16	3000	202.0	201.0	28.0
TS3A5018RSVR	UQFN	RSV	16	3000	184.0	184.0	19.0

## D (R-PDS0-G16)

#### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



## D (R-PDSO-G16)

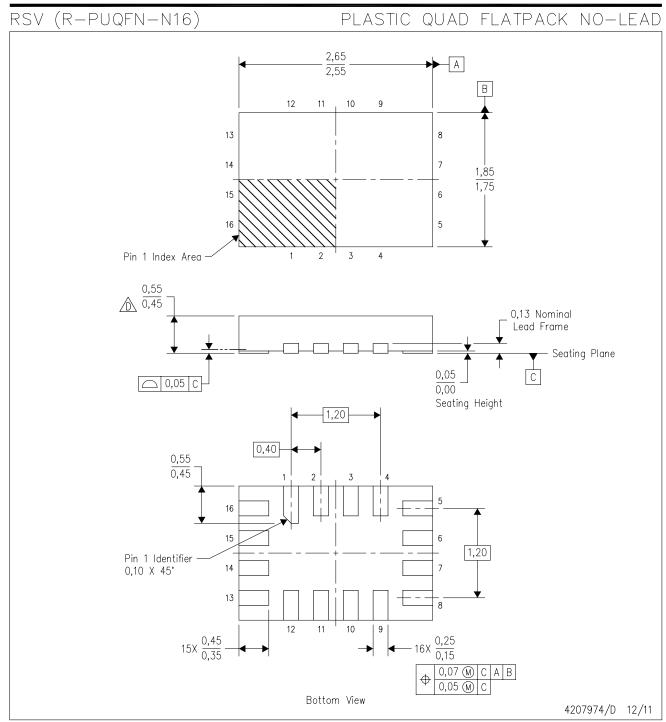
## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





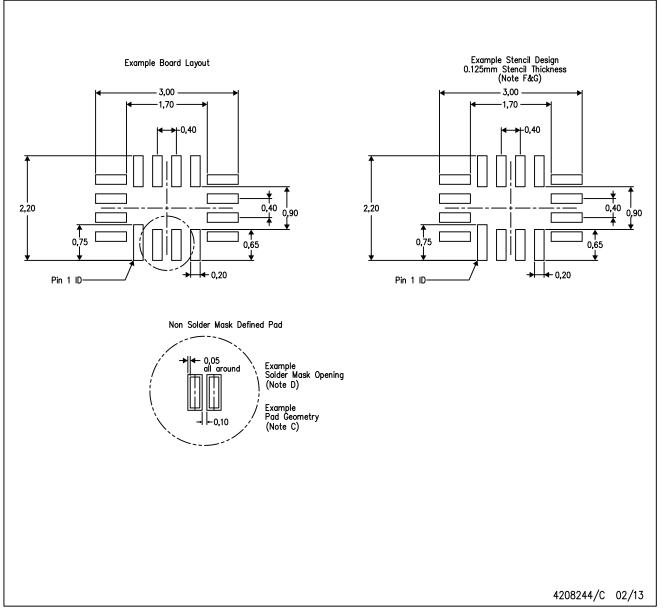
NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- This package complies to JEDEC MO-288 variation UFHE, except minimum package thickness.



## RSV (R-PUQFN-N16)

#### PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A.

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over—print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



PW (R-PDSO-G16)

#### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



## PW (R-PDSO-G16)

## PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







#### NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



## RGY (R-PVQFN-N16)

#### PLASTIC QUAD FLATPACK NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



## RGY (R-PVQFN-N16)

## PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



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